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Main Entry: 2size Function: verh

Inflected Form(s): sized: siz-ing

Date: 1609 transitive senses

1: to make a particular size: bring to proper or suitable size

2: to arrange, grade, or classify according to size or hulk

intransitive senses: to equal in size or other particular characteristic: COMPARE -- usually used with up and often with to or with

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PAT-NO:

JP407221070A

DOCUMENT-IDENTIFIER: JP 07221070 A

TITLE:

DRY ETCHING METHOD

PUBN-DATE:

August 18, 1995

INVENTOR - INFORMATION: NAME KADOMURA, SHINGO

ASSIGNEE-INFORMATION: NAME

SONY CORP

COUNTRY

N/A

APPL-NO: JP06008348

APPL-DATE: January 28, 1994

INT-CL (IPC): H01L021/3065, H01L021/28

## ABSTRACT:

PURPOSE: To provide an anisotropic dry etching method of platinum laver used for an electrode etc., of a semiconductor device using a ferroelectric thin film.

CONSTITUTION: Pt-base metal layer 3 is subjected to dry etching while heating and controlling a substrate temperature to 90°C or can release liberated sulfur into plasma such as S<SB>2</SB>F<SB>2</SB>. Since the deposit of sulfur or sulfur compound such as polythiazyl is utilized as a side-wall protection film 6. anisotropy is improved. Since a substrate is heated within a specific temperature range, a practical etching rate can

DOCUMENT-IDENTIFIER: US 20030129866 A1

TITLE: Spring metal structure with passive-conductive coating on tip

----- KWIC -----

Summary of Invention Paragraph - BSTX (10): [0007] In accordance with a second embodiment of the present invention. methods for fabricating microspring structures are disclosed in which a conductive coating (e.g., a refractory noble metal such as Rhodium (Rh), Iridium (Ir), Rhenium (Re), Platinum (Pt), and Palladium (Pd)) is deposited on the tip of the free (i.e., cantilevered) portion of the spring metal finger using an intermediate mask that is patterned between the formation (etching) of the spring finger and the release of the spring finger. A first mask is formed over sequentially formed release and spring metal layers that is used to etch the underlying spring metal and release layers to form a spring metal island formed on a release material island. The second mask is then formed with a window that exposes a tip of the spring metal island. In one embodiment, the second mask is photoresist formed with undercut (i.e., negative sloped) walls to facilitate liftoff of the passive-conductive coating formed on the upper surface of the second mask. To prevent the formation of a flange that may undesirably secure (anchor) the tip to the underlying substrate, the spring structure is briefly immersed in a release material etchant to remove the release material located under the tip prior to the deposition of the passive-conductive coating. The passive-conductive coating